

L Number	Hits	Search Text	DB	Time stamp
4	5	09/360292	USPAT; US-PGPUB	2004/03/03 08:18
5	184313	(trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)	USPAT; US-PGPUB	2004/03/03 08:32
6	8052	((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))	USPAT; US-PGPUB	2004/03/03 10:47
7	2415	((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma))	USPAT; US-PGPUB	2004/03/03 10:49
8	556	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with hydrogen))	USPAT; US-PGPUB	2004/03/03 08:29
9	561	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))	USPAT; US-PGPUB	2004/03/03 10:50
10	135	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with hydrogen)) and (plasma with (chlorine 'cl'))	USPAT; US-PGPUB	2004/03/03 08:30
11	137	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))) and (plasma with (chlorine 'cl'))	USPAT; US-PGPUB	2004/03/03 10:50
12	137	((((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))) and (plasma with (chlorine 'cl')) and (trench groove hole via opening recess damascene etch\$3 insulat\$ dielectric etching hydrogen chlorine plasma substrate silicon))	USPAT; US-PGPUB	2004/03/03 12:16
13	19	((((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))) and (plasma with (chlorine 'cl')) and (trench groove hole via opening recess damascene etch\$3 insulat\$ dielectric etching hydrogen chlorine plasma substrate silicon)) and ((trench groove hole via opening recess damascene) with (silicide refractory))	USPAT; US-PGPUB	2004/03/03 12:16
14	1	10/039517	USPAT; US-PGPUB	2004/03/03 09:14
15	2057	((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((clean\$3 remov\$4) near4 plasma))	USPAT; US-PGPUB	2004/03/03 10:49
16	2616	((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((clean\$3 remov\$4 treat\$2 treatment) near4 plasma))	USPAT; US-PGPUB	2004/03/03 10:49
17	932	((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((clean\$3 remov\$4 treat\$2 treatment) near4 plasma))) and (gas near4 plasma))	USPAT; US-PGPUB	2004/03/03 10:49
18	330	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((clean\$3 remov\$4 treat\$2 treatment) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2'))	USPAT; US-PGPUB	2004/03/03 10:50
19	80	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((clean\$3 remov\$4 treat\$2 treatment) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))) and (plasma with (chlorine 'cl' 'cl.sub.2'))	USPAT; US-PGPUB	2004/03/03 12:11

21	8	(((((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((clean\$3 remov\$4 treat\$2 treatment) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))) and (plasma with (chlorine 'cl' 'cl.sub.2')))) and (trench groove hole via opening recess damascene etch\$3 insulat\$ dielectric etching hydrogen chlorine plasma substrate silicon)) and ((trench groove hole via opening recess damascene) with (silicide refractory))	USPAT; US-PGPUB	2004/03/03 12:17
20	80	(((((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((clean\$3 remov\$4 treat\$2 treatment) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))) and (plasma with (chlorine 'cl' 'cl.sub.2')))) and (trench groove hole via opening recess damascene etch\$3 insulat\$ dielectric etching hydrogen chlorine plasma substrate silicon)	USPAT; US-PGPUB	2004/03/03 13:31

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4	5	09/360292	USPAT; US-PGPUB	2004/03/03 08:18
5	184313	(trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)	USPAT; US-PGPUB	2004/03/03 08:32
6	8052	((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))	USPAT; US-PGPUB	2004/03/03 08:27
7	2415	((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)	USPAT; US-PGPUB	2004/03/03 08:28
8	556	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with hydrogen)	USPAT; US-PGPUB	2004/03/03 08:29
9	561	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2'))	USPAT; US-PGPUB	2004/03/03 08:30
10	135	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with hydrogen)) and (plasma with (chlorine 'cl'))	USPAT; US-PGPUB	2004/03/03 08:30
11	137	(((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))) and (plasma with (chlorine 'cl'))	USPAT; US-PGPUB	2004/03/03 08:30
12	137	((((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))) and (plasma with (chlorine 'cl')))) and (trench groove hole via opening recess damascene etch\$3 insulat\$ dielectric etching hydrogen chlorine plasma substrate silicon)	USPAT; US-PGPUB	2004/03/03 08:31
13	19	((((((trench groove hole via opening recess damascene) with (etch\$3 insulat\$ dielectric)) and ((trench groove hole via opening recess damascene) with ((etch\$3 clean\$3 remov\$4) near4 plasma))) and (gas near4 plasma)) and (plasma with (hydrogen 'h2')))) and (plasma with (chlorine 'cl')))) and (trench groove hole via opening recess damascene etch\$3 insulat\$ dielectric etching hydrogen chlorine plasma substrate silicon)) and ((trench groove hole via opening recess damascene) with (silicide refractory))	USPAT; US-PGPUB	2004/03/03 09:14
14	1	10/039517	USPAT; US-PGPUB	2004/03/03 09:14

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 BRS form
 IS&R form
 Image
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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030236003 A1	20031225	32	Method of forming barrier layer of semiconductor device	438/795	438/533; 438/653;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030015496 A1	20030123	9	PLASMA ETCHING PROCESS	216/67	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20020040886 A1	20020411	9	Chemical vapor deposition process of depositing a material over a semico	216/2	216/37; 216/67
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020040885 A1	20020411	9	Plasma etching process and semiconductor plasma etching proces	216/2	216/67
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6511575 B1	20030128	46	Treatment apparatus and method utilizing negative hydrogen ion		204/298.34; 204/298.36
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6335282 B1	20020101	8	Method of forming a titanium comprising layer and method of formi	438/682	257/E21.165; 257/E21.168;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6001736 A	19991214	26	Method of manufacturing semiconductor device and an apparat	438/677	118/718; 118/723MP;

22. (1278) 22 and (plasma nears hydrogen)

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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030236003 A1	20031225	32	Method of forming barrier layer of semiconductor device	438/795	438/533; 438/653;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030015496 A1	20030123	9	PLASMA ETCHING PROCESS	216/67	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20030013313 A1	20030116	23	Process for fabricating semiconductor device	438/706	257/E21.252; 438/689;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020040886 A1	20020411	9	Chemical vapor deposition process of depositing a material over a semico	216/2	216/37; 216/67
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20020040885 A1	20020411	9	Plasma etching process and semiconductor plasma etching proces	216/2	216/67
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20010012694 A1	20010809	13	Plasma etching method using low ionization potential gas	438/689	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20010006245 A1	20010705	130	Manufacturing method of semiconductor integrated circuit devi	257/513	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6645870 B2	20031111	21	Process for fabricating semiconductor device	438/710	257/E21.252; 438/700;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6607988 B2	20030819	123	Manufacturing method of	438/720	438/3

